## NUP3105L, SZNUP3105L

## **ESD Protection Diode**

### **Dual Line CAN Bus Protector**

The SZ/NUP3105L has been designed to protect the CAN transceiver in 24 V systems from ESD and other harmful transient voltage events. This device provides bidirectional protection for each data line with a single compact SOT-23 package, giving the system designer a low cost option for improving system reliability and meeting stringent EMI requirements.

#### Features

- 350 W Peak Power Dissipation per Line (8/20 µsec Waveform)
- Low Reverse Leakage Current (< 100 nA)
- Low Capacitance High-Speed CAN Data Rates
- IEC Compatibility: IEC 61000-4-2 (ESD): Level 4
  - IEC 61000–4–4 (EFT): 50 A 5/50 ns
  - IEC 61000-4-5 (Lighting) 8.0 A (8/20 μs)
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### Applications

- Industrial Control Networks
  - Smart Distribution Systems (SDS<sup>®</sup>)
  - ♦ DeviceNet<sup>TM</sup>
- Automotive Networks
  - Low and High-Speed CAN
  - Fault Tolerant CAN
  - Trucks



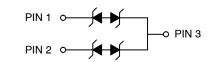
#### **ON Semiconductor®**

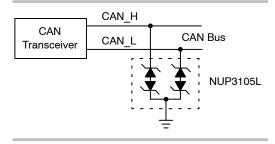
www.onsemi.com

#### SOT-23 DUAL BIDIRECTIONAL VOLTAGE SUPPRESSOR 350 W PEAK POWER

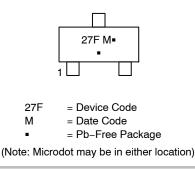


SOT-23 CASE 318 STYLE 27





#### MARKING DIAGRAM



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

#### NUP3105L, SZNUP3105L

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C, unless otherwise specified)

Symbol	Rating	Value	Unit
PPK	Peak Power Dissipation 8 x 20 μs Double Exponential Waveform (Note 1)	350	W
TJ	Operating Junction Temperature Range	–55 to 150	°C
TJ	Storage Temperature Range	-55 to 150	°C
ΤL	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body model (HBM) Machine Model (MM) IEC 61000-4-2 Specification (Contact)	8.0 400 30	kV V kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 1.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}$ C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V <sub>RWM</sub>	Reverse Working Voltage	(Note 2)	-	-	32	V
$V_{BR}$	Breakdown Voltage	I <sub>T</sub> = 1 mA (Note 3)	35.6	-	-	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>RWM</sub> = 32 V	-	-	100	nA
V <sub>C</sub>	Clamping Voltage	I <sub>PP</sub> = 5 A (8/20 μs Waveform) (Note 4)	-	-	59	V
V <sub>C</sub>	Clamping Voltage	I <sub>PP</sub> = 8 A (8/20 μs Waveform) (Note 4)	-	-	66	V
I <sub>PP</sub>	Maximum Peak Pulse Current	8/20 μs Waveform (Note 4)	-	-	8.0	А
CJ	Capacitance	$V_R = 0 V$ , f = 1 MHz (Line to GND)	_	-	30	pF

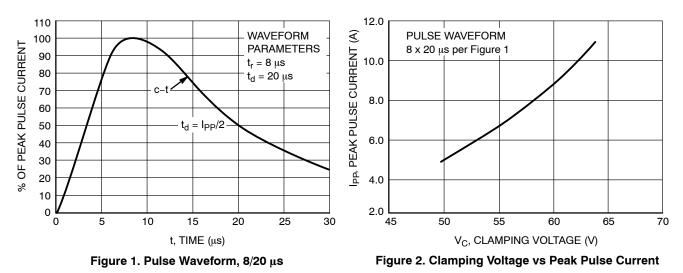
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Surge protection devices are normally selected according to the working peak reverse voltage (V<sub>RWM</sub>), which should be equal or greater 2. than the DC or continuous peak operating voltage level.

3.  $V_{BR}$  is measured at pulse test current I<sub>T</sub>. 4. Pulse waveform per Figure 1.

#### **TYPICAL PERFORMANCE CURVES**

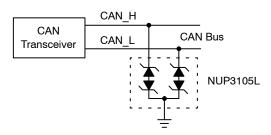
 $(T_{,l} = 25^{\circ}C \text{ unless otherwise noted})$ 



#### **Surge Protection Diode Protection Circuit**

Surge protection diodes provide protection to a transceiver by clamping a surge voltage to a safe level. surge protection diodes have high impedance below and low impedance above their breakdown voltage. A surge protection Zener diode has its junction optimized to absorb the high peak energy of a transient event, while a standard Zener diode is designed and specified to clamp a steady state voltage.

Figure 3 provides an example of a dual bidirectional surge protection diode array that can be used for protection with the high–speed CAN network. The bidirectional array is created from four identical Zener surge protection diodes. The clamping voltage of the composite device is equal to the breakdown voltage of the diode that is reversed biased, plus the diode drop of the second diode that is forwarded biased.



#### Figure 3. High–Speed and Fault Tolerant CAN Surge Protection Circuit

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NUP3105LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZNUP3105LT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NUP3105LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZNUP3105LT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

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#### MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

## onsemi



SCALE 4:1

A\_\_\_\_ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

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DETAIL A

END VIEW

DATE 01 MAR 2023

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*





XXX = Specific Device Code

M = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

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### MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

# onsemi

#### SOT-23 (TO-236) CASE 318 ISSUE AT

#### DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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